

Application No. 10/044,974
Amendment dated September 30, 2003
Reply to Office Action of July 29, 2003

Amendments To The Specification

In accordance with Rule 1.121(b)(2), please replace the section on page 3 extending from line 6 through line 16 with:

BRIEF DESCRIPTION OF DRAWINGS

The invention will be described in detail in the following description of preferred embodiments with reference to the following figures wherein:

FIGS. 1-3 are section views through an isolated photodiode according to three embodiments of the present invention;

FIG. 4 is a potential well diagram representing the electric potential along a line through the photodiode region of the isolated photodiodes of FIGS. 1 and 2;

FIG. 5 is a section view through an alternative isolated photodiode according to the present invention; [and]

FIG. 6 is a potential well diagram representing the electric potential along a cutline through the surface gated photodiode region of the isolated photodiode of FIG. 5;

FIGS. 7-9 are section views through the isolated photodiodes of FIGS. 1-3 except with the depth of the implant beneath the photodiode increased; and

FIGS. 10-12 are section views through the isolated photodiodes of FIGS. 1-3 except with isolated photodiodes formed in a lightly doped epi that is disposed on the substrate.